

I hereby certify that this correspondence is being
Electronically Transmitted on the date noted below to:

Commissioner for Patents

P.O. Box 1450

Alexandria, VA 22313-1450

March 18, 2011

Date of Deposit

Jasper W. Dockrey, Reg. No. 33,868

Name of applicant, assignee or

Registered Representative

/Jasper W. Dockrey/

Signature

March 18, 2011

Date of Signature

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Appln. of: Nguyet-Phuong Nguyen et al.

Appln. No.: 10/577,175

Filed: April 3, 2007

For: METHOD FOR SELF-
SUPPORTED TRANSFER OF
A FINE LAYER BY PULSATION
AFTER IMPLANTATION OR
CO-IMPLANTATION

Attorney Docket No: 9905/40 (BIF116533US)

Examiner: Luke, Daniel M.

Art Unit: 2813

Confirmation No.: 3451

THIRD SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents

PO Box 1450

Alexandria, VA 22313-1450

In accordance with the duty of disclosure under 37 CFR §1.56 and §§1.97-1.98,
and more particularly in accordance with 37 CFR §1.97(b), Applicants hereby cite the
following reference(s):

U.S. PATENT DOCUMENTS		
DOCUMENT NO.	DATE	NAME
3,901,423	08/1975	Hillberry, et al.
3,915,757	10/1975	Engel
3,957,107	05/1976	Altoz et al.
3,993,909	11/1976	Drews et al.

4,006,340	02/1977	Gorinas
4,039,416	08/1977	White
4,074,139	02/1978	Pankove
4,107,350	08/1978	Berg et al.
4,108,751	08/1978	King
4,121,334	10/1978	Wallis
4,170,662	10/1979	Weiss et al.
4,179,324	12/1979	Kirkpatrick
4,244,348	01/1981	Wilkes
4,252,837	02/1981	Auton
4,274,004	06/1981	Kanai
4,324,631	08/1982	White et al.
4,346,123	08/1982	Kaufmann
4,361,600	11/1982	Brown
4,368,083	01/1983	Bruel et al.
4,412,868	11/1983	Brown et al.
4,452,644	06/1984	Bruel et al.
4,468,309	08/1984	White
4,471,003	09/1984	Cann
4,486,247	12/1984	Ecer et al.
4,490,190	12/1984	Speri
4,500,563	02/1985	Ellenberger et al.
4,508,056	04/1985	Bruel et al.
4,536,657	08/1985	Bruel
4,539,050	09/1985	Kramler et al.
4,542,863	09/1985	Larson
4,566,403	01/1986	Fournier
4,567,505	01/1986	Pease
4,568,563	02/1986	Jackson et al.
4,585,945	04/1986	Bruel et al.
4,630,093	12/1986	Yamaguchi et al.
4,684,535	08/1987	Heinecke et al.
4,704,302	11/1987	Bruel et al.
4,717,683	01/1988	Parrillo et al.
4,764,394	08/1988	Conrad
4,837,172	06/1989	Mizuno et al.
4,846,928	07/1989	Dolins et al.
4,847,792	07/1989	Barna et al.
4,853,250	08/1989	Boulos et al.
4,887,005	12/1989	Rough et al.
4,891,329	01/1990	Reisman et al.
4,894,709	01/1990	Phillips et al.
4,904,610	02/1990	Shyr
4,920,396	04/1990	Shinohara et al.
4,929,566	05/1990	Beitman
4,931,405	06/1990	Kamijo et al.
4,948,458	08/1990	Ogle
4,952,273	08/1990	Popov
4,956,698	09/1990	Wang
4,960,073	10/1990	Suzuki et al.
4,975,126	12/1990	Margail et al.

4,982,090	01/1991	Wittmaack
4,996,077	02/1991	Moslehi et al.
5,013,681	05/1991	Godbey et al.
5,015,353	05/1991	Hubler et al.
5,034,343	07/1991	Rouse et al.
5,036,023	07/1991	Dautremont-Smith et al.
5,110,748	05/1992	Sarma
5,120,666	06/1992	Gotou
5,138,422	08/1992	Fujii et al.
5,198,371	03/1993	Li
5,200,805	04/1993	Parsons et al.
5,232,870	08/1993	Ito et al.
5,234,535	08/1993	Beyer et al.
5,250,446	10/1993	Osawa et al.
5,256,581	10/1993	Foerstner et al.
5,259,247	11/1993	Bantien
5,310,446	05/1994	Konishi et al.
5,413,951	05/1995	Ohori et al.
5,442,205	08/1995	Brasen et al.
5,494,835	02/1996	Bruel
5,524,339	06/1996	Gorowitz et al.
5,539,241	07/1996	Abidi et al.
5,567,654	10/1996	Beilstein, Jr. et al.
5,611,316	03/1997	Oshima et al.
5,618,739	04/1997	Takahashi et al.
5,622,896	04/1997	Knotter et al.
5,633,174	05/1997	Li
5,661,333	08/1997	Bruel et al.
5,714,395	02/1998	Bruel
5,741,733	04/1998	Bertagnolli et al.
5,753,038	05/1998	Vichr et al.
5,804,086	09/1998	Bruel
5,817,368	10/1998	Hashimoto
5,863,830	01/1999	Bruel et al.
5,863,832	01/1999	Doyle et al.
5,880,010	03/1999	Davidson
5,882,987	03/1999	Srikrishnan
5,897,331	04/1999	Sopori
5,981,400	11/1999	Lo
5,985,412	11/1999	Gösele
6,010,591	01/2000	Gösele
6,013,954	01/2000	Hamajima
6,020,252	02/2000	Aspar et al.
6,033,974	03/2000	Henley et al.
6,054,363	04/2000	Sakaguchi et al.
6,057,212	05/2000	Chan et al.
6,080,640	06/2000	Gardner et al.
6,096,433	08/2000	Kikuchi et al.
6,118,181	09/2000	Merchant et al.
6,156,215	12/2000	Shimada et al.
6,159,323	12/2000	Joly et al.

6,197,695 B1	03/2001	Joly et al.
6,198,159 B1	03/2001	Hosoma et al.
6,200,878 B1	03/2001	Yamagata et al.
6,204,079 B1	03/2001	Aspar et al.
6,225,192 B1	05/2001	Aspar et al.
6,251,754 B1	06/2001	Ohshima et al.
6,276,345 B1	08/2001	Nelson et al.
6,287,940 B1	09/2001	Cole et al.
6,294,478 B1	09/2001	Shkaguchi et al.
6,306,720 B1	10/2001	Ding
6,310,387 B1	10/2001	Seefeldt et al.
6,316,333 B1	11/2001	Bruel et al.
6,362,082 B1	03/2002	Doyle et al.
6,407,929 B1	06/2002	Hale et al.
6,417,075 B1	07/2002	Haberger et al.
6,429,094 B1	08/2002	Maleville et al.
6,429,104 B1	08/2002	Auberton-Herve
6,465,892 B1	10/2002	Suga
6,504,235 B2	01/2003	Schmitz et al.
6,529,646 B1	03/2003	Wight et al.
6,548,375 B1	04/2003	De Los Santos et al.
6,596,569 B1	07/2003	Bao et al.
6,632,082 B1	10/2003	Smith
6,645,831 B1	11/2003	Shaheen et al.
6,645,833 B2	11/2003	Brendel
6,653,207 B2	11/2003	Ohya et al.
6,756,285 B1	06/2004	Moriceau et al.
6,762,076 B2	07/2004	Kim et al.
6,764,936 B2	07/2004	Daneman et al.
6,774,010 B2	08/2004	Chu et al.
6,809,009 B2	10/2004	Aspar et al.
6,828,214 B2	12/2004	Notsu et al.
6,846,690 B2	01/2005	Farcy et al.
6,887,769 B2	05/2005	Kellar et al.
6,893,936 B1	05/2005	Chen et al.
6,902,987 B1	06/2005	Tong et al.
6,927,147 B2	08/2005	Fitzgerald et al.
6,947,365 B2	09/2005	Lai et al.
6,974,759 B2	12/2005	Moriceau et al.
6,991,956 B2	01/2006	Ghyselen et al.
7,018,909 B2	03/2006	Ghyselen et al.
7,029,548 B2	04/2006	Aspar et al.
7,029,980 B2	04/2006	Liu et al.
7,067,396 B2	06/2006	Aspar et al.
7,078,811 B2	07/2006	Suga
7,256,075 B2	08/2007	Ghyselen et al.
7,348,260 B2	03/2008	Ghyselen
7,416,957 B2	08/2008	Ponomarev
7,459,374 B2	12/2008	Aulnette et al.
7,465,646 B2	12/2008	Le Vaillant
7,476,596 B2	01/2009	Lieber et al.

7,494,897 B2	02/2009	Fournel et al.
7,498,234 B2	03/2009	Aspar et al.
7,521,292 B2	04/2009	Rogers et al.
7,534,701 B2	05/2009	Ghyselen et al.
7,615,463 B2	11/2009	Aspar et al.
7,670,930 B2	03/2010	Tauzin et al.
7,713,369 B2	05/2010	Aspar et al.
7,772,087 B2	08/2010	Nguyen et al.
7,883,994 B2	02/2011	Moriceau et al.
7,902,038 B2	03/2011	Aspar et al.
RE39,484 E	02/2007	Bruel
2001/0007367 A1	07/2001	Ohkubo
2001/0007789 A1	07/2001	Aspar et al.
2002/0000646 A1	01/2002	Gooch et al.
2002/0081861 A1	06/2002	Robinson et al.
2002/0145489 A1	10/2002	Cornett et al.
2002/0185469 A1	12/2002	Podlesnik et al.
2002/0083387 A1	06/2002	Miner et al.
2002/0001221 A1	01/2003	Fischer et al.
2003/0119279 A1	06/2003	Enquist
2003/0119280 A1	06/2003	Lee et al.
2006/0252229 A1	11/2006	Joly et al.
2006/0281212 A1	12/2006	Moriceau et al.
2007/0037363 A1	02/2007	Aspar et al.
2007/0281445 A1	12/2007	Nguyen et al.
2008/0254591 A1	10/2008	Deguet et al.
2009/0120568 A1	05/2009	Deguet et al.
2009/0130392 A1	05/2009	Aspar et al.
2009/0156016 A1	06/2009	Di Cioccio
2010/0025228 A1	02/2010	Tauzin et al.
2010/0167499 A1	07/2010	Fournel et al.
2010/0216294 A1	08/2010	Rabarot et al.
2010/0323497 A1	12/2010	Fournel

FOREIGN PATENT DOCUMENTS		
DOCUMENT NO.	DATE	COUNTRY
EP 0 355 913 A1	02/1990	EPO
EP 0 383 391 A1	08/1990	EPO
EP 0 504 714 A2	09/1992	EPO
EP 0 660 140 A1	06/1995	EPO
EP 0 665 588 A1	08/1995	EPO
EP 0 703 609 A1	03/1996	EPO
EP 0 754 953 B1	01/1997	EPO
EP 0 849 788 A2	06/1998	EPO
EP 0 889 509 A2	01/1999	EPO
EP 0 895 282 A2	02/1999	EPO
EP 0 898 307 A1	02/1999	EPO
EP 0 989 593 A2	03/2000	EPO
EP 1 059 663 A2	12/2000	EPO
EP 1 096 259 A1	05/2001	EPO
DE 101 53 319 A1	05/2003	GERMANY

FR 95 08882	06/1996	FRANCE
FR 2 558 263 A1	07/1985	FRANCE
FR 2 671 472 A1	07/1992	FRANCE
FR 2 725 074 A1	03/1996	FRANCE
FR 2 736 934 A1	01/1997	FRANCE
FR 2 767 604 A1	02/1999	FRANCE
FR 2 771 852 A1	06/1999	FRANCE
FR 2 789 518 A1	08/2000	FRANCE
FR 2 819 099 A1	07/2002	FRANCE
GB 2 211 991 A	07/1989	GREAT BRITAIN
JP 53-104156 A	09/1978	JAPAN
JP 58-031519 A	02/1983	JAPAN
JP 59-054217 A	03/1984	JAPAN
JP 61-129872 A	06/1986	JAPAN
JP 01-128570 A	05/1989	JAPAN
JP 01-169917 A	07/1989	JAPAN
JP 04-199504 A	07/1992	JAPAN
JP 08-017777 A	01/1990	JAPAN
JP 08-133878 A	05/1996	JAPAN
JP 10-163166 A	06/1998	JAPAN
JP 10-233352 A	09/1998	JAPAN
JP 11-317577 A	11/1999	JAPAN
SU 128757 A1	06/2000	RUSSIA
WO 95/20824 A1	08/1995	WIPO
WO 01/43168 A2	06/2001	WIPO
WO 02/05344A1	01/2002	WIPO
WO 03/021667 A2	03/2003	WIPO
WO 03/063213 A2	07/2003	WIPO

OTHER ART – NON PATENT LITERATURE DOCUMENTS

Agarwal, Aditya et al. "Efficient Production of Silicon-On-Insulator Films by Co-Implantation of He+ with H+" – Proceedings 1997 IEEE International SOI Conference, October 1997 – pp. 44-45.
Ahn, K. Y., et al., "Growth, Shrinkage, And Stability of Interfacial Oxide Layers Between Directly Bonded Silicon Wafers", Applied Physics A., Vol. 50, 1990, pp 85-94.
Alley et al., "Surface Roughness Modification of Interfacial Contacts In Polysilicon Microstructures", Proceedings of the 7th International Conference on Solid-State Sensors and Actuators, Transducers '93, PACIFICO, Yokohama JAPAN. Jun 7-10, 1993, pp 288-291.
Almedia et al. "Bond formation in ion beam synthesized amorphous gallium nitride", Elsevier, This Solid Films, 343-344 1999, pp 632-636.
Ascheron, C., "A Comparative Study of Swelling, Radiation, Strain and Radiation Damage of High-Energy Proton-bombarded GaAs, GaP, InP, Si and Ge Single Crystals, Nuclear Instruments and Methods in Physics Research", Nuclear Instruments and Methods In Physics Research B36, (1989), 163-172.
Ascheron, C., "A Study of Proton Bombardment Induced Swelling of GaP Single Crystals", Phys. stat. sol. (a) 92, (1985), pp 169-176.
Ascheron, C., "Gettering a Copper in Proton-and Helium-Bombarded Buried Regions of Gallium Phosphide", Phys. stat. sol. (a), Vol. 106, 1988, pp 73-79.
Ascheron, C., "Investigations of Hydrogen Implanted GaP Single Crystals by Means of Particle Induced 7-Spectroscopy, Infrared Spectroscopy, and Turyherford Backscattering Channeling Technique" Phys. stat. sol. (a) 89, (1985), pp 549.

Ascheron, C., "Proton Beam Modification of Selected AlIBV Compounds", Phys. stat. sol. (a) 124, (1991), pp 11.
Ascheron, C., "Swelling, Strain, and Radiation Damage of He+ Implanted GaP", Phys. stat. sol. (a) 96, 1986, pp. 555-562. (1986).
Ascheron, C., "The Effect of Hydrogen Implantation Induced Stress on GaP Single Crystals", Nuclear Instruments and Methods in Physics Research, B28 (1987), pp 350-359.
Aspar et al., "The Generic Nature of the Smart-Cut® Process for Thin-Film Transfer", Journal of Electronic Materials, Vol. 30, No. 7, March - 2001, pp 834-840.
Aspar et al., Smart-Cut®: The basic fabrication process for UNIBOND® SOI wafers, SEMI 1996, pp. 37-46.
Aspar, B. "Basic Mechanisms Involved in the Smart-Cut Process", 1997, pp. 223-240.
Aspar, B. et al, "Characterization of SOI substrates: Application to Recent SIMOX and UNIBOND Wafers," Electrochemical Society Proceedings, vol. 96-3, pp. 99-111, January 1996.
Aspar, B. et al, "Transfer of Structured and Patterned Thin Silicon Films Using the Smart-Cut Process", 1996, pp. 1985-1986.
Aspar, B. Et al., "Ultra Thin Buried Oxide Layers Formed By Low Dose SIMOX Processes", Proc. 6th International Conference on SOI Technology and Devices, Electro. Soc., Vol. 94, No. 11, 1994, pp 62-69.
Aspar, B. et al., "Smart Cut – Process Using Metallic Bonding: Application to Transfer of Si, GaAs, InP Thin Films", Electronic Letters – June 10, 1999, Vol. 35, No. 12., pp. 1024-1025.
Ashurst et al., "Water Level Anti-Silicon Coatings For MEMS", Sensors and Actuators A104, 2003, pp 213-221.
Auberton-Herve, A. J. et al, "A New Sal Material: Smart-Cut", 1996, pp.214-219.
Auberton-Herve et al., "SOI Materials for ULSI Applications", Semiconductor International, Oct. 1995, 5 pages.
Auberton-Herve, "Why Can Smart Cut® Change The Future Of Microelectronics?" published in International Journal of High Speed Electronics and Systems, Vol. 10, No. 1 (2000) pgs. 131-146.
Ayguavives et al., "Physical Properties of (Ba,Sr) TiO3 Thin Films Used for Integrated Capacitors in Microwave Applications", IEEE 2001.
Blanchard-Lagahe C. et al., "Hydrogen and Helium Implantation to Achieve Layer Transfer" Vol. 19, pp. 346-358, 2003, Semiconductor Wafer Bonding VII: Science, Technology, and Applications – Proceedings of the International Symposium.
Blöchl P.E. et al., "First-Principles Calculations of Diffusion Coefficients: Hydrogen in Silicon, Physical Review Letters, Vol. 64, No. 12, 1990, pp 1401-1404.
Borgati, Stephen P., "The Root-Mean-Square", Boston College, Nov. 16, 1998, Obtained from the Internet at: < http://www.analytictech.com/mb313/rootmean.htm >.
Bruel, Michel, "Application of Hydrogen Ion Beams To Silicon on Insulator Material Technology", Nuclear Instruments and Methods in Physics Research, B108, 1996, pp 313-319.
Bruel, M. et al., "Smart-Cut: A New Silicon on Insulator Material Technology Based on Hydrogen Implantation and Wafer Bonding", 1997, pp. 1636-1641, Col. 36, Part 1, No. 3B.
Bruel, M. "Smart-Cut Process: The Way to Unibond S.O.I. Wafers", 1996, pages unknown.
Bruel, M. et al, "Smart-Cut": A Promising New SOI material technology, Proceedings 1994 IEEE, International Sal Conference, Oct. 1995, pp. 178-179.
Bruel, M. et al, "Smart-Cut-a new SOI Material Technology based on hydrogen Implantation and wafer bonding," CEA, 1996, 24 pages.
Bruel, M., "Silicon on insulator Material Technology", Electronic Letters; 31 (1995) Jul. 6; No. 14; pp. 1201-1202.
Bruel, M., "Silicon-an-Insulator", European Semiconductor, Mar. 1997.
Canham et al. "Radiative Recombination Channels due to Hydrogen In Crystalline Silicon", Materials Science and Engineering, B4 (1989) pp. 41-45.
Carter et al., "Applications of Ion Beams to Materials", Inst. Phys. Conf. Ser., No. 28, Chapter 1, 1976, pp 30-36.

Carter, G. et al., "The Collection of Ions Implanted In Semiconductors: II Range Distributions Derived From Collection and Sputter-Etch Curves, Radiation Effects, 1972, Vol. 16, pp 107-114.
Cassidy, Victor M., "Ion Implantation Process Toughens Metalworking Tools," Modern Metals, 1984, pp. 65-67.
Cerofolini et al., "Hydrogen-Related Complexes as the Stressing Species in High-Fluence, Hydrogen-Implanted, Single-Crystal Silicon" Physical Review B, vol. 46, No.4, 1992, pp. 2061-2070.
Cerofolini et al., "Hydrogen and Helium Bubbles In Silicon", Material Science and Engineering 2000 – Reports: A Review Journal, Published By Elsevier Science S.A. 2000, pp. 1-52.
Chu et al, "Radiation Damage of 50-250 keV Hydrogen Ions in Silicon", Ion Implantation in Semiconductors, eds. F. Chernob et al., Plenum New York 1976, pp. 483-492.
Chu, et al. "Ion Implantation In Semiconductors", Chernow, Borders and Brice, Pirnum Press, New York and London. Radiation Damage of 50-250 keV Hydrogen Ions in Silicon, 1976, pp. 483-491.
Chu, P.K. et al., "Plasma Immersion Ion Implantation-A Fledgling Technique for Semiconductor Processing", Materials Science and Engineering Reports", A Review Journal, vol. R17, Nos. 6-7, Nov. 30, 1996, pp. 207-280.
Cowern, N. et al., "Transport Diffusion of Ion-Implanted B In Si: Dose, Time, and Matrix Dependence of Atomic and Electrical Profiles", J. Appl. Phys., Vol. 68, No. 12, 1990, pp 6191-6198.
Cristoloveanu, S. et al, "Electrical Properties of Unibond Material", Electrochemical Society Proceedings, Vol. 96-3, pp. 142-147, 1996.
Csepregi, L. et al. "Regrowth Behavior of Ion-Implanted Amorphous Layers on <111> Silicon", Applied Physics Letters, Vol. 2, 1976, pp 92-93.
Cullis, A.G. et al. "Comparative study of annealed neon-, argon-, and krypton-ion implantation damage in silicon," J. Appl. Phys., 49(10), Oct. 1978, pp. 5188-5198.
Denteneer, P. et al., "Hydrogen Diffusion and Passivation of Shallow Impurities in Crystalline Silicon, Materials Science Forum, Trans Tech Publications, Switzerland, Vols. 38-41, 1989, pp 979-984.
Denteneer, P. et al., "Structure and Properties of Hydrogen-Impurity Pairs in Elemental Semiconductors", Physical Review Letters, Vol. 62, No. 16, 1989, pp 1884-1888.
Di Cioccio, L. et al., "Silicon Carbide On Insulator Formation By The Smart Cut® Process". – Materials Science and Engineering B46 (1997) – (pgs. 349-356).
DiCioccio, et al., "Silicon carbide on Insulator formation using the Smart Cut process", Electronics Letters, vol. 32, No. 12, Jun. 6, 1996, pp. 1144-1145.
Diem et al., "SOI 'SIMOX': From Bulk To Surface Micromachining, A New Age For Silicon Sensors and Actuators", Sensors and Actuators, Vol. A 46-47, 1995, pp 8-16.
Dirks, A. G. et al., "Columnar Microstructure In Vapor DEuropesited Thin Films ", Thin Solid Films, Vol. 47, 1977, pp 219-233.
Donohue et al., "Pulse-Extended Excimer Laser Annealing of Lead Zirconate Titanate Thin Films", Proceedings of the 12th International Symposium on Integrated Ferroelectrics, Aachen, Germany, March 2000, Integrated Ferroelectrics, vol. 31, pages 285 to 296, 2000.
Duo, et al., "Comparison Between The different Implantation orders in H+ and He+ Co-implantation", J. Phys. D. Appl. Phys. Vol. 34, 2001, pp 477-482.
Duo, et al., "Evolution of Hydrogen and Helium Co-Implanted Single-Crystal Silicon During Annealing", 2001 American Institute Physics – Journal of Applied Physics, Vol. 90, No. 8, October 15, 2001, pp. 3780-3786.
Eaglesham, White, Feldman, Moriya And Jacobson, "Equilibrium Shape of Si," Physical Review Letters, vol. 70, No. 11, Mar. 15, 1993, pp. 1643-1646.
EerNisse, E., "Compaction of ion-implanted fused silica", Journal of Applied Physics, vol. 45, No.1, Jan. 1974.

EerNisse, E.P., "Role of Integrated Lateral Stress In Surface Deformation of He- Implanted Surfaces" Journal of Applied Physics, vol. 48, No.1, Jan. 1977, pp 9-17.
Evans, J.H., "An Interbubble Fracture Mechanism Of Blister Formation On Helium-Irradiated Metals" Journal of Nuclear Materials, 68, 1977, pp 129-140.
Fujitsuka et al., "A New processing Technique To Prevent Stiction Using Silicon Selective Etching For SOT-MEMS", Sensors and Actuators, A97-98, 2002, pp 716-719.
Garnier, D. M., "The Fabrication Of A Partial Soi Substrate", Proceedings of the 9th International Symposium On Silicon On Isolator Technology and Devices, Vol. 99, Chap. 54, 1990, 73-78.
Gerasimenko, N., "Infrared Absorption of Silicon Irradiated by Protons", Phys. stat.sol. (b) 90, (1978), pp 689-695.
Ghandi, Sorab, "VLSI Fabrication Princiles-Silicon And Gallium Arsenide", Rensselaer Polytechnic Institute, 1983, John Wiley & Sons publishers, pp 135.
Goesele et al., "Semiconductor Wafer Bonding", Science and Technology, ECS Series, Annual Review of Material Science, Vol, 28, New Jersey, 1999, pp 215-241.
Greenwald, A.C., "Pulsed-electron-beam annealing of ion-implantation damage", J. Appl. Phys. 50(2), Feb. 1978, pp. 783-786.
Grovenor, C.R.M., Microelectronic Materials, pp. 73-75 (1989).
Guilhalmenc, C. et al, "Characterization By Atomic Force Microscopy of the SOI Layer Topography in Low Dose SIMOX Materials", Materials Science and Engineering, B46, 1997, pp 29-32.
Haisma et al., Silicon-on-Insulator Wafer Bonding-Wafer Thinning Technological Evaluations", JAPANese Journal of Applied Physics, 28, 1989, Aug., No.8, Part 1, Tokyo, JAPAN, pp. 1426-1443.
Hamaguchi et al., "Device Layer Transfer Technique using Chemi-Mechanical Polishing", JAPANese Journal of Applied Physics, 23,(1984), Oct., No. 10, Part 2, Tokyo, JAPAN, pp. L815-L817.
Heistand et al., "Advances in Passive Integration for C/RC Arrays & Networks with Novel Thin & Thick Film Materials", 36th Nordic IMAPS Conference, Helsinki, 1999.
Hendrix et al., "Low-Temperature Process for High-Density Thin-Film Integrated Capacitors", International Conference on High-Density Interconnect and Systems Packaging, 2000.
Huang, et al., "Calculation of critical layer thickness considering thermal strain in Si1-xGex/Si strained-layer heterostructures, J. Appl. Phys. 83 (1), January 1, 1998.
Hulett, D.M. et al., "Ion Nitriding and Ion Implantation: A Comparison," Metal Progress, 1985, pp. 18-21.
IBM Technical Disclosure Bulletin, Isolation by Inert Ion Implantation, 1986, vol. 29 No. 3, pp 1416.
IBM Technical Disclosure Bulletin, SOI Interposer Structure XP 000627972, July 1996, vol. 39 No. 7, pp. 1-5.
Jalaguier, E. et al., "Transfer of Thin InP Films Onto Silicon Substrate By Proton Implantation Process". – 11th International Conference on Indium Phosphide and Related Materials 16-20 May 1999 – Davos, Switzerland. (pgs. 26-27)
Jalaguier, E. et al., "Transfer of 3in GaAs Film on Silicon Substrate By Proton Implantation Process". – (2 pgs).
Jaussaud, C. et al., 'Microstructure of Silicon Implanted With High Dose Oxygen Ions', Appl. Phys. Lett., Vol. 48, No. 11, 1985, pp 1064-1066.
Jenei et al., "High-Q Inductors and Capacitors on Si Substrate", IEEE 2001.
Johnson, "High Fluence Deuteron Bombardment of Silicon", Radiation Effects, vol. 32, pp. 159-167, 1977.
Jones, K. S. et al., "A Systematic Analysis of Defects In Ion Implanted Silicon", Applied Physics A., Vol. 45, 1988 pp 1-34.
Jones et al., "Enhanced elimination of implantation damage upon exceeding the solid solubility", J. App. Phys., Vol. 62, No. 10, 1987, pp 4114-4117.

Kamada et al, "Observation of Blistering and Amorphization on Germanium Surface After 450 keV Ar+ION Bombardment, Radiation Effects, vol. 28, 1976, pp. 43-48.
Kim et al., "A Porous-Si-based Novel Isolation Technology for Mixed-Signal Integrated Circuits", Symposium on VLSI Technology, 2000.
Klem, J.F., "Characteristics of Lift-Off Fabricated AlGaAs/InGaAs Single-Strained-Quantum Well Structures On Glass and Silicon Substrates", Inst. Phys. Conf. Ser. No. 96: Chapter 6, (1989), pp. 387-392.
Komarov et al., "Crystallographic Nature and Formation Mechanisms of Highly Irregular Structure in Implanted and Annealed S1, Layers Radiation Effects, vol. 42, 1979, pp. 169-178.
Laporte A. et al., "Charged Defects At The Interface Between Directly Bonded Silicon Wafers" – Applied Physics, Vol. 36 (September 1997) pp. 5502-5506-Part 1, No. 9A.
Li, J., "Novel Semiconductor Substrate Formed by Hydrogen Ion Implantation into Silicon," Appl. Phys. Lett., vol. 55, No. 21, Nov. 20, 1989, pp. 2223-2224.
Ligeon, E., "Hydrogen Implantation in Silicon Between 1.5 and 60 KeV", Radiation Effects 1976, vol. 27, pp. 129-137.
Liu et al., "Investigation of Interface In Silicon-On-Insulator By Fractal Analysis", Applied Surface Science, Vol. 187, Feb 28, 2002, pp 187-191.
Liu et al., "Integrated Thin Film Capacitor Arrays", International Conference on High Density Packaging and MCMs, 1999.
Lu, X., et al., "SOI Material Technology Using Plasma Immersion ION Implantation", Proceedings 1996 IEEE International SOI Conference, October 1996, pp. 48-49.
Maleville, C. et al, "Physical Phenomena involved in the Smart-Cut Process", Electrochemical Society Proceeding, vol. 96-3, 1996 - pp. 34-46.
Maleville, C. et al, "Wafer Bonding and Hi-Implantation Mechanisms Involved In The Smart-Cut Technology", 1997, pp 14-19.
Manuaba, A., "Comparative Study on Fe ₃₂ Ni ₃₆ Cr ₁₄ P ₁₂ B ₆ Metallic Glass and its Polycrystalline Modification bombarded by 2000 keV Helium Ions with High Fluence" Nuclear Instruments and Methods, (1982) pp 409-419.
Mastrangelo, C. et al., "Suppression of Stiction in MEMS", Proceedings of the Materials Research Society Seminar, Vol. 605, 2000, pp 1-12.
Matsuda et al., "Large Diameter Ion Beam Implantation System," Nuclear Instruments and Methods, vol. B21, 1987, pp. 314-316.
Matsuo et al., "Abnormal solid solution and activation behavior in GA-implanted Si(100)", Appl. Phys. Lett., Vol. 51, No. 24, 1987, pp 2037-2039.
Mishima, Y. and T. Yagishita, T. "Investigation of the bubble formation mechanism in a-Si:H films by Fourier-transform infrared microspectroscopy" J. Appl. Phys., vol. 64, No.8, Oct. 15, 1988, pp3972-3974.
Miyagawa, S. et al, "Helium Reemission During Implantation of Silicon Carbide", J. Appl. Phys., 54 (5), May 1983, pp. 2302-2306.
Miyagawa, S., "Surface structure of silicon carbide Irradiated with helium ions with mono energy and continuous energy distributions" J. Appl. Phys. 53(12), Dec. 1982, pp. 8697-8705.
Monemar, B. "Shallow Impurities in Semiconductors 1998", Proceedings of the Third International Conference in Sweden, Aug. 10-12, 1988, No. 95, pp 493-499.
Moreau, Wayne M., "Semiconductor Lithography, Principles, Practices, and Materials," Plenum Press, 1988. Table of Contents only. Moriceau, H. et al, A New Characterization Process Used to Qualify SOI Films 1991 pp. 173-178.
Moriceau, H. et al, "A New Characterization Process Used to Qualify SOI Films", Electrochemical Society Proceedings, Volume 99-3, 1999 pp. 173-178.
Moriceau, H. et al, "A New Characterization Process Used to Qualify SOI Films", Abstract No. 405, Meeting Abstracts, The Electrochemical Society, Inc., Vol. 99-1, Seattle, May 2-6, 1999, 2 pages.
Moriceau, H. et al. "Cleaning and Polishing As Key Steps For Smart-Cut SOI Process", Proceedings 1996 IEEE SOI Conference, Oct. 1996.

Moriceau, H. et al, "The Smart-Cut Process as a Way to Achieve Specific Film Thickness in Sal Structures", 1997, pages unknown.
Motohiro et al. "Geometrical Factors of Argon Incorporation In SiO ₂ Films Deposited By ION Beam Sputtering" – Thin Solid Films, Elsevier-Sequoia S.A. Lausanne, CH, Vol. 120, No. 4 – October 1, 1984 (1984-10-01), pgs. 313-327.
Munteanu, D. et al, "Detailed Characterization of Unibond Material", 1997, pp. 395-398.
Myers, D. R., "The effects of Ion-Implantation damage on the first order Raman spectra GaPa" J. Appl. Phys. 54(9), Sep. 1977.
Nethling, J. et al, "Identification of Hydrogen Platelets in Proton Bombarded GaAs", 1985, pp. 941-945.
Nichols C. S et al., "Properties of Hydrogen in Crystalline Silicon Under Compression and Tension", Physical Review Letters, Vol. 63, No. 10, 1989, pp 1090-1093.
Nicoletti, S. et al., "Bi-Epitaxial YBCO Grain Boundry Josephson Junctions on SrTiO ₃ and Sapphire Substrates", Physics C269, 1996, pp 255-267.
Ono et al., "Orientation Dependence of Flaking of Ion Irradiated Aluminum Single Crystals", Japanese Journal of Applied Physics, vol. 25, No., 10, 1986, pp. 1475-1480.
Paszti, E, "Flaking and Wave-Like Structure on Metallic Glasses Induced by MeV-Energy Helium Ions", Nuclear Instruments and Methods, Vol. 209/210, (1983), pp. 273-280.
Picraux, S. Thomas et al., "Ion Implantation of Surfaces," Scientific American, vol. 252, No.3, pp. 102-113 1985.
Popov, V.P. et al., "Blistering On A Silicon Surface in the Process of Sequential Hydrogen/Helium ION Co-plantation" – Optoelectronics Instrumentation and Data Processing, No. 3, April 5, 2001 - pp. 90-98 – 2001.
Primak, W., "Impurity Effect in the Ionization Dilation of Vitreous Silica" J. Appl. Phys. 39(13) 1968.
Ray et al. "Effect of Reactive-Ion Bombardment on the Properties of Silicon Nitride and Oxynitride Films Deposited By Ion-Beam Sputtering" – Journal of Applied Physics, Vol. 75, No. 12, June 15, 1994 – pgs. 8145-8152.
Renier, M. et al., "A New Low-Energy Ion Implanter for Bombardment of Cylindrical Surfaces," Vacuum, vol. 35, No. 12, pp. 577-578, 1985.
Roozeboom et al., "High-Value MOS Capacitor Arrays in Ultradeep Trenches in Silicon", Microelectronic Engineering, vol. 53, pages 581 to 584, Elsevier Science 2000.
Roth, J., "Blistering and Bubble Formation" Inst. Phys. Conf. Ser. No. 28, 1976: Chapter 7, pp 280-293.
Sah, Chih -Tang et al., "Deactivation of the Boron Acceptor in Silicon by Hydrogen," Appl. Phys. Lett. 43, (2), Jul. 1983, pp. 204-206
Saint-Jacques R. G., "La Formation des Cloques", Nuclear Instruments and Methods, No. 209/210", North Holland Publishing Co., 1983, pp 333-343.
Schnell et al., "Plasma Surface Texturization for Multicrystalline Silicon Solar Cells", IEEE, XXVIII, Photovoltaic Conference, 2000, pp 367-370.
Shintani, A. et al., "Temperature dependence of stresses in chemical deposited vitreous films", J. Appl. Phys., Vol. 51, No. 8, 1980, pp 4197.
Silicon-On-Insulator, European Semiconductor, Mar. 1997, pp. 17-18.
Sioshansi, Piran, "Ion Beam Modification of Materials for Industry," Thin Solid Film, vol. 118, 1984, pp. 61-71.
Snyman, H. C., "Transmission Electron Microscopy of Extended Crystal Defects in Proton Bombarded and Annealed GaAs", Radiation Effects, 1983, vol. 69, pp. 199-230.
Snyman, H. C. et al, "Void Formation in Annealed Proton-Bombarded GaAs", 1981, pp. 243-245.
Stein, Myers and Follstaedt, "Infrared Spectroscopy of chemically bonded hydrogen at voids and defects in silicon", J. Appl. Phys. 73(b6), Mar. 15, 1993, pp. 2755-2764.
Stephen, D., "Investigation of Lattice Strain in Proton-Irradiated GaP by a Modified Auleytner Technique" Phys. stat. sol. (a) 87, 1985, pp. 589- 596.

Sunkara et al., "Bulk synthesis of silicon nanowires using a low-temperature vapor-liquid-solid solution", Applied Physics Letters, Vol. 79, No. 10, September 3, 2001, pp 1546-1548.
Sze, S.M., VLSI Technology, 2.sup.nd Ed., 1988, pp. 9-10.
Tan, T. Y. et al., "On Oxygen Precipitation Retardation/Recovery Phenomena, Nucleation Incubation Phenomena and The Exigent-Accommodation-Volume Factor of Precipitation", Proceedings of the 5th International Symposium On Silicon Materials Science and Technology, Semiconductor Silicon 198 Electrochem. Soc., New Jersey, 1986, pp 864-873.
Terada, K. et al., "A New Dram Cell With A Transistor On A Lateral Epitaxial Silicon Layer (Tol Cell)", IEEE Transactions On Electron Device, Vol. 37, No. 9, 1990, pp 2052-2057.
Theodore, N. David et al., "TFSOI With Improved Oxidation Resistance (To Reduce Isolation Induced Stresses and Leakage), Motorola Bulletin XP 000691920, Technical Developments, Nov. 1996, pp 158-59.
Tillman et al., "Zero-Level Packaging for MEMS or MST Devices: The IRS Method", MEMS/Sensors, Advancing Microelectronics, Pages 37-39, November/December 2000.
Tomisaka et al., "Electroplating Cu Fillings for Through-Vias for Three-Dimensional Chip Stacking" (Electronic Components and Technology Conference, 2002).
Tonini, Monelli, Corni, Ottaviani, Frabboni, Canteri, Queirolo, "Hydrogen Interaction with phosphorus ion implanted silicon", Ion Implantation Technology -94, (1995) pp. 801-804.
Tzeng, J.C., "A Novel Self-Aligned Oxygen (Salox) Implanted SOI Mosfet Device Structure" Nuclear Instruments and Methods in Physics Research B2, 1987, pp. 112-115.
U.S. Dept. of Energy, "The Fusion Connection: Contributions to Industry, Defense, and Basic Science Resulting From Scientific Advances Made in the Magnetic Fusion Energy Program", Plasma Coating, pp. 6-7, 1985.
Van de Walle, C. "Structural Identification of Hydrogen and Muonium Centers in Silicon First Principles Calculations of Hyperfine Parameters", Physical Review Letters, Vol. 60, No. 26, 1988, pp 2761-2764.
Van de Walle, C. "Theoretical Aspects of Hydrogen in Crystalline Semiconductors", Physica B, Holland, Vol. 170, No. 15, 1991, pp 21-32.
Van de Walle, C. "Theory of Hydrogen Diffusion and Reactions in Crystalline Silicon", Physical Review Letters, Vol. 64, No. 6, 1980, pp 669-672.
Van de Walle, C. "Theory of Hydrogen Diffusion and Reactions in Crystalline Silicon", Physical Review B, Vol. 39, No. 15, 1989, pp 10 791-10 808, plus diagrams.
Van Swijgenhoven et al. "Helium Bubble and Blister Formation for Nickel and An Amorphous Fe-Ni-Mo-B Alloy During 5 kev He+-Irradiation at Temperatures Between 200 K and 600", Nuclear Instruments and Methods, 209/210, 1983, pp. 461-468.
Veldkamp, W.B. et al., "Binary Optics," Scientific American, 1992, pp. 50-55.
Venezia et al., "The Role of Implantation Damage in the Production of Silicon-On-Insulator Films By Co-Implantation Of He+ and H+", Electrochemical Society Proceedings Volume 98-1, 1998 - pp. 1384-1395.
Weldon et al., "Mechanism Of Silicon Exfoliation Induced by Hydrogen/Helium Co-implantation", Applied Physics Letters, Vol, 73, No. 25, pp 3721-3723, Dec 21, 1998.
Wemple, S.H., "Optical and channeling studies of ion-bombarded GaP", J. Appl. Phys., vol. 45, No.4, Apr. 1974, pp 1578-1588.
Whitton, J. L. et al., "The Collection of Ions Implanted In Semiconductors: 1 Saturations Effects", Radiation Effects, Scotland, Vol. 16, 1972, pp 101-105.
Wiegand, M. et al., "Wafer Bonding of Silicon Wafers Covered With Various Surface Layers", Sensors and Actuators, Elsevier Science B.V., Vol. 86, 2000, pp 91-95.
Williams J. et al., "Annealing behaviour of high-dose rare-gas implantations into silicon", from Application of Ion Beams to Materials, 1975, Chap. 1, Inst. Phys. Conf. Ser. No. 28, 1976, pp 30-36.
Wittmaack et al., "High Fluence Retention of Noble Gases Implanted in Silicon" Radiation Effects, vol. 39, 1978, pp. 81-95.

Wolf, Stanley Ph.D., Silicon Processing for the VLSI Era (vol. 2), Lattice Press, 1990, pp. 66-79.
Yamaguchi H. et al., "Intelligent Power IC With Partial Soi Structure", Jpn. J. Appl. Phys., Vol. 34, 1995, pp 864-868.
Yee et al., "Polysilicon Surface-Modification Technique to Reduce Sticking of Microstructures", Sensors and Actuators A 52, 1996, pp. 145-150.
Yun, H. et al., "Transfer of Patterned Ion-Cut Silicon Layers", Applied Physics Letters, Vol. 73, No. 19, 1998, pp 2772-2774.
International Search Report for International Application No. PCT/FR1998/002904, dated April 16, 1999, 2 pages.
International Search Report for International Application No. PCT/FR2002/003422, dated January 22, 2003, 3 pages.
International Search Report for International Application No. PCT/FR2003/003256, dated March 19, 2004, 6 pages.
International Search Report for International Application No. PCT/FR2003/003867, dated May 28, 2004, 3 pages.
International Search Report for International Application No. PCT/FR2003/003622, dated June 3, 2004, 3 pages.
International Search Report for International Application No. PCT/FR2004/001858, dated December 28, 2004, 3 pages.
International Search Report for International Application No. PCT/FR2004/002779, dated April 5, 2005, 3 pages.
International Search Report for International Application No. PCT/FR2004/002781, dated April 5, 2005, 3 pages.
International Search Report for International Application No. PCT/FR2004/001565, dated July 6, 2005, 3 pages.
International Search Report for International Application No. PCT/FR2006/002184, dated January 24, 2007, 2 pages.
International Search Report for International Application No. PCT/FR2007/000534, dated November 22, 2007, 3 pages.
International Search Report for International Application No. PCT/FR2007/002100, dated February 4, 2009, 3 pages.
International Search Report for International Application No. PCT/FR2008/001427, dated July 1, 2009, 3 pages.
Office Action from US Application No. 12/063,808, dated April 6, 2010, 9 pages.
Office Action from US Application No. 12/063,808, dated September 22, 2010, 9 pages.
Office Action from US Application No. 10/534,199, dated February 19, 2009, 8 pages.
Office Action from US Application No. 10/534,199, dated August 5, 2009, 10 pages.
Office Action from US Application No. 10/534,199, dated January 20, 2010, 8 pages.
Office Action from US Application No. 10/534,199, dated August 4, 2010, 8 pages.
Office Action from US Application No. 11/480,250, dated May 22, 2008, 10 pages.
Office Action from US Application No. 11/480,250, dated December 3, 2008, 16 pages.
Office Action from US Application No. 11/480,250, dated January 26, 2010, 14 pages.
Office Action from US Application No. 11/480,250, dated August 3, 2010, 15 pages.
Office Action from US Application No. 12/088,047, dated September 25, 2009, 9 pages.
Office Action from US Application No. 12/088,047, dated March 10, 2010, 9 pages.
Office Action from US Application No. 10/561,299, dated March 26, 2008, 9 pages.
Office Action from US Application No. 10/561,299, dated December 9, 2008, 11 pages.
Office Action from US Application No. 10/561,299, dated May 11, 2009, 12 pages.
Office Action from US Application No. 10/561,299, dated November 16, 2009, 11 pages.
Office Action from US Application No. 10/561,299, dated November 27, 2009, 10 pages.
Office Action from US Application No. 10/561,299, dated May 11, 2010, 11 pages.

Office Action from US Application No. 10/565,621, dated May 15, 2007, 13 pages.
Office Action from US Application No. 10/565,621, dated February 11, 2008, 11 pages.
Office Action from US Application No. 10/565,621, dated September 12, 2008, 9 pages.
Office Action from US Application No. 10/565,621, dated March 12, 2009, 6 pages.
Office Action from US Application No. 10/565,621, dated January 7, 2010, 8 pages.
Office Action from US Application No. 10/565,621, dated November 23, 2010, 11 pages.
Office Action from US Application No. 12/628,772, dated October 7, 2010, 12 pages.
Notice of Allowance from US Application No. 12/336,229, dated September 29, 2010, 7 pages.
Notice of Allowance from US Application No. 12/336,229, dated January 10, 2011, 4 pages.
Office Action from US Application No. 10/468,223, dated October 5, 2005, 7 pages.
Office Action from US Application No. 10/468,223, dated May 3, 2006, 11 pages.
Office Action from US Application No. 10/468,223, dated January 10, 2007, 11 pages.
Office Action from US Application No. 10/468,223, dated July 20, 2007, 11 pages.
Office Action from US Application No. 10/468,223, dated February 11, 2008, 11 pages.
Office Action from US Application No. 10/468,223, dated October 29, 2008, 11 pages.
Office Action from US Application No. 10/468,223, dated June 25, 2009, 8 pages.
Notice of Allowance from US Application No. 10/468,223, dated December 28, 2009, 4 pages.
Office Action from US Application No. 10/474,984, dated September 24, 2004, 6 pages.
Office Action from US Application No. 10/474,984, dated June 6, 2005, 5 pages.
Office Action from US Application No. 10/474,984, dated November 16, 2005, 5 pages.
Office Action from US Application No. 10/474,984, dated May 17, 2006, 5 pages.
Office Action from US Application No. 10/474,984, dated May 7, 2007, 9 pages.
Office Action from US Application No. 10/474,984, dated February 6, 2008, 10 pages.
Office Action from US Application No. 10/474,984, dated October 17, 2008, 11 pages.
Office Action from US Application No. 10/474,984, dated July 7, 2009, 10 pages.
Office Action from US Application No. 10/474,984, dated March 11, 2010, 13 pages.
Notice of Allowance from US Application No. 10/474,984, dated October 28, 2010, 6 pages.
Office Action from US Application No. 10/540,303, dated December 18, 2007, 6 pages.
Notice of Allowance from US Application No. 10/540,303, dated October 7, 2008, 9 pages.
Office Action from US Application No. 11/327,906, dated October 1, 2007, 5 pages.
Office Action from US Application No. 11/327,906, dated February 11, 2008, 5 pages.
Notice of Allowance from US Application No. 11/327,906, dated September 15, 2008, 6 pages.
Office Action from US Application No. 10/975,826, dated September 2, 2009, 24 pages.
Notice of Allowance from US Application No. 10/975,826, dated April 28, 2010, 8 pages.
Office Action from US Application No. 10/492,343, dated October 17, 2005, 6 pages.
Office Action from US Application No. 10/492,343, dated June 6, 2006, 13 pages.
Office Action from US Application No. 10/492,343, dated November 14, 2006, 13 pages.
Office Action from US Application No. 10/492,343, dated May 29, 2007, 15 pages.
Office Action from US Application No. 10/492,343, dated February 7, 2008, 18 pages.
Office Action from US Application No. 10/492,343, dated August 18, 2008, 12 pages.
Office Action from US Application No. 10/492,343, dated December 22, 2008, 9 pages.
Notice of Allowance from US Application No. 10/492,343, dated June 26, 2009, 6 pages.
Office Action from US Application No. 11/747,733, dated March 16, 2009, 9 pages.
Office Action from US Application No. 11/747,733, dated March 23, 2010, 5 pages.
Notice of Allowance from US Application No. 11/747,733, dated September 29, 2010, 8 pages.
Notice of Allowance from US Application No. 12/293,193, dated October 8, 2009, 10 pages.
Expert Report of Marcus Weldon, Ph.D. dated November 1, 2000
Expert Report of Jean-Pierre Colinge dated November 1, 2000.
Expert Report of Chris Van de Walle, Ph.D. dated November 1, 2000
Memorandum in Support of Defendant Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated March 19, 2001

Memorandum of Points and Authorities In Support of Soitec's Motion for Summary Judgment on Sigen's Enablement Invalidity Claim (Redacted) dated March 27, 2001
Soitec's Memorandum of Points and Authorities In Opposition to Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated April 11, 2001
Memorandum in Support of Defendant Silicon Genesis Corporation's Opposition to Soitec's Motion for Summary Judgment on SiGen's Defense of Enablement dated April 20, 2001
Reply Memorandum in Support of Defendant Silicon Genesis Corporation's Motion for Summary Judgment of Invalidity for Lack of Enablement dated April 30, 2001
Expert Report of Marcus Weldon, Ph.D. dated August 24, 2001
Report of Jean-Pierre Colinge in Response to SiGen Enablement and Indefiniteness Expert Reports of August 24, 2001
Expert Report of Chris Van de Walle, Ph.D. dated August 24, 2001
Memorandum and Order re: Summary Judgment [denied] dated February 5, 2002
Plaintiff's Memorandum in Support of Their Motion for Judgment As a Matter of Law and a New Trial dated May 10, 2002
Silicon Genesis Corporation's Opposition to Plaintiff's Motion for Judgment as a Matter of Law and a New Trial dated June 17, 2002
Memorandum of Law in Support of Plaintiff's Motion for Judgment on SiGen's Indefiniteness Defense dated June 20, 2002
Plaintiff's Reply Memorandum in Support of Their Motion for Judgment as a Matter of Law and a New Trial dated July 18, 2002
Defendant Silicon Genesis Corporation's Opposition to Soitec's Motion for Judgment Re Indefiniteness and Cross-Motion for Judgment of Indefiniteness dated July 19, 2002
Plaintiff's Reply in Support of their Motion for Judgment on SiGen's Indefiniteness Defense dated July 25, 2002
Memorandum and Order re: Post-Trial Motions dated August 23, 2002
Judgment dated October 21, 2002.
Brief of Plaintiffs-Appellants Soitec, S.A. and Commissariat a L'Energie Atomique dated January 28, 2003
Brief for Defendant-Cross Appellant Silicon Genesis Corporation dated March 22, 2003
Reply Brief of Plaintiffs-Appellants Soitec, S.A. and Commissariat a L'Energie Atomique dated May 5, 2003
Reply Brief for Defendant-Cross Appellant Silicon Genesis Corporation dated May 19, 2003
Plaintiff/Appellants Supplemental Authority Letter [dated November 17, 2003].
Defendant-Cross Appellant's Response To Appellants' Submission Of CFMT, Inc. v. Yieldup Int'l, [dated November 24, 2003].
Decision from the United States Court of Appeals for the Federal Circuit dated November 26, 2003.
Combined Petition for Panel Rehearing and for Rehearing En Banc by Plaintiffs-Appellant's Soitec, S.A. and Commissariat A L'Energie Atomique, dated December 10, 2003.
Order [dated January 7, 2004 denying Appellants' petition for panel rehearing and Appellant's petition for rehearing en banc].
Judgment Mandate [dated January 14, 2004].
NOTICE of by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique re <u>30</u> MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution MOTION to Dismiss Based upon Fed. R. Civ. P. 12(b)(1) and (6) and Article III of the United States Constitution Notice of Withdrawal of Plaintiffs' Partial Motion to Dismiss Counterclaim Counts II, III, IV, V, and VIII (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2009)
STIPULATION and [Proposed] Order to File an Amended Complaint by SOITEC Silicon On Insulator Technologies SA, Commissariat a LEnergie Atomique. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/16/2009)

NOTICE OF SERVICE of Soitec's Objections and Responses to MEMC's Second Request For Production of Documents and Things Directed To Soitec re <u>46</u> Notice of Service by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. Related document: <u>46</u> Notice of Service filed by MEMC Electronic Materials Inc. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/16/2009)
First AMENDED COMPLAINT for Patent Infringement against MEMC Electronic Materials Inc.- filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Exhibit Exhibit 1, # <u>2</u> Exhibit Exhibit 2, # <u>3</u> Exhibit Exhibit 3, # <u>4</u> Exhibit Exhibit 4, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 07/21/2009)
ANSWER to Amended Complaint ANSWER to <u>57</u> Amended Complaint, with Under Federal Rule of Civil Procedure 38, MEMC demands a trial by jury on all issues so triable., COUNTERCLAIM against all plaintiffs by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2009)
ANSWER to <u>60</u> Answer to Amended Complaint, Counterclaim,,, COUNTERCLAIM Reply to Defendant's Amended Counterclaims, Counterclaims And Affirmative Defenses against MEMC Electronic Materials Inc. by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/31/2009)
NOTICE OF SERVICE of MEMC's THIRD SET OF INTERROGATORIES DIRECTED TO S.O.I.TEC SILICON ON INSULATOR TECHNOLOGIES, S.A., SOITEC USA, INC., AND COMMISSARIAT A L'ENERGIE ATOMIQUE by MEMC Electronic Materials Inc. (Rogowski, Patricia) (Entered: 09/01/2009)
ANSWER to <u>68</u> Answer to Counterclaim,,, by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 09/14/2009). Minute Entry for proceedings held before Judge Sue L. Robinson - Discovery Conference held on 9/16/2009. (Court Reporter V. Gunning.) (nmf) (Entered: 09/16/2009)
MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 10/20/2009). CORRECTING ENTRY: Docket clerk deleted D.I. 78 (opening brief) due to document being filed improperly. Counsel is advised to re-file document using the OPENING BRIEF event code rather than the combined opening and answering brief event code. (lid) (Entered: 10/21/2009)
OPENING BRIEF in Support re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 11/9/2009. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C)(Rogowski, Patricia) (Entered: 10/21/2009)
Cross MOTION to Bifurcate all Collateral Issues - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a L'Energie Atomique. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)
ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues, <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by SOITEC Silicon On Insulator Technologies SA, Commissariat a L'Energie Atomique.Reply Brief due date per Local Rules is 11/20/2009. (Attachments: # <u>1</u> Exhibit, # <u>2</u> Exhibit, # <u>3</u> Exhibit, # <u>4</u> Exhibit, # <u>5</u> Exhibit, # <u>6</u> Exhibit, # <u>7</u> Exhibit, # <u>8</u> Exhibit, # <u>9</u> Exhibit, # <u>10</u> Exhibit, # <u>11</u> Exhibit, # <u>12</u> Declaration, # <u>13</u> Certificate of Service)(Kraft, Denise) (Entered: 11/09/2009)
REPLY BRIEF re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3)(Rogowski, Patricia) (Entered: 11/17/2009)
ANSWERING BRIEF in Opposition re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 12/3/2009. (Rogowski, Patricia) (Entered: 11/19/2009)

REPLY BRIEF re <u>85</u> Cross MOTION to Bifurcate all Collateral Issues filed by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit Declaration of Marcus T. Hall in Support of Plaintiffs' Reply Re: Cross-Motion to Bifurcate all Collateral Issues)(Kraft, Denise) (Entered: 12/03/2009)
NOTICE OF SERVICE of S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Production of Three Boxes of Wafer Samples by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/08/2009). Set Hearings: Discovery Conference set for 12/21/2009 04:00 PM in Courtroom 6B before Judge Sue L. Robinson. (nmf) (Entered: 12/09/2009).
MOTION for Leave to File Stipulated Motion for Leave to File a Sur-Reply Brief in Support of MEMC's Motion to Bifurcate - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 12/14/2009)
SUR-REPLY BRIEF re <u>77</u> MOTION to Bifurcate the Issues of Willfulness and Damages for Purposes of Discovery and Trial and proposed Form of Order MEMC's SUR-REPLY BRIEF IN SUPPORT OF ITS MOTION TO BIFURCATE THE ISSUES OF WILLFULNESS AND DAMAGES FOR PURPOSES OF DISCOVERY AND TRIAL filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/16/2009)
MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 05/07/2010)
OPENING BRIEF in Support re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 5/24/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6, # <u>7</u> Exhibit 7, # <u>8</u> Exhibit 8, # <u>9</u> Exhibit 9, # <u>10</u> Exhibit 10, # <u>11</u> Exhibit 11, # <u>12</u> Exhibit 12, # <u>13</u> Exhibit 13, # <u>14</u> Exhibit 14, # <u>15</u> Exhibit 15)(Rogowski, Patricia) (Entered: 05/07/2010)
ANSWERING BRIEF in Opposition re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA.Reply Brief due date per Local Rules is 6/4/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
DECLARATION re <u>145</u> Answering Brief in Opposition,, Declaration of Marcus T. Hall in Support of Plaintiff's Answering Brief in Opposition to Defendant's Motion For the Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 05/24/2010)
REPLY BRIEF IN SUPPORT OF <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Exhibit 3, # <u>4</u> Exhibit 4, # <u>5</u> Exhibit 5, # <u>6</u> Exhibit 6)(Rogowski, Patricia) Modified on 6/4/2010 (lid). (Entered: 06/04/2010)
STATEMENT re <u>148</u> Stipulation Joint Claim Construction Statement by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)
CLAIM Construction Chart by Commissariat a L'Energie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/14/2010)

<p>SUR-REPLY BRIEF re <u>141</u> MOTION for Discovery MOTION FOR THE ADMISSION OF THE EXPERT TESTIMONY OF JOHN T. GOOLKASIAN RELATING TO THE CERTIFICATE OF CORRECTION FOR U.S. PATENT NO. 7,067,396 Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian filed by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)</p>
<p>DECLARATION re <u>157</u> Sur-Reply Brief, Declaration of Marcus T. Hall in Support of Surreply by Plaintiffs to Motion by Defendant For The Admission of Expert Testimony of John T. Goolkasian by SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Certificate of Service)(Kraft, Denise) (Entered: 06/15/2010)</p>
<p>CLAIM CONSTRUCTION OPENING BRIEF filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0001-DA0006, # <u>2</u> Appendix DA0007-DA0032, # <u>3</u> Appendix DA0033-DA0072, # <u>4</u> Appendix DA0073-DA0112, # <u>5</u> Appendix DA0113-DA0152, # <u>6</u> Appendix DA0153-DA0192, # <u>7</u> Appendix DA0193-DA0232, # <u>8</u> Appendix DA0233-DA0272, # <u>9</u> Appendix DA0273-DA0312, # <u>10</u> Appendix DA0313-DA0352, # <u>11</u> Appendix DA0353-DA0392, # <u>12</u> Appendix DA0393-DA0432, # <u>13</u> Appendix DA0433-DA0472, # <u>14</u> Appendix DA0473-DA0512, # <u>15</u> Appendix DA0513-DA0521, # <u>16</u> Appendix DA0522-DA0545, # <u>17</u> Appendix SEALED - DA0546-DA0551, # <u>18</u> Appendix DA0552-DA0563, # <u>19</u> Appendix SEALED - DA0564-DA0566, # <u>20</u> Appendix DA0567-DA0573, # <u>21</u> Appendix SEALED - DA0574-DA0599, # <u>22</u> Appendix DA0600-DA0604, # <u>23</u> Appendix DA0605-DA0609, # <u>24</u> Appendix DA0610-DA0625, # <u>25</u> Appendix DA0626-0634, # <u>26</u> Appendix DA0635, # <u>27</u> Appendix DA0636-DA0652, # <u>28</u> Appendix SEALED - DA0653-DA0657, # <u>29</u> Appendix DA0658-DA0667, # <u>30</u> Appendix DA0668-DA0670, # <u>31</u> Appendix DA0671-DA0678, # <u>32</u> Appendix DA0679-DA0687, # <u>33</u> Appendix DA0688-DA0696, # <u>34</u> Appendix SEALED - DA0697-DA0705, # <u>35</u> Appendix SEALED - DA0706-DA0711, # <u>36</u> Appendix SEALED - DA0712-DA0714, # <u>37</u> Appendix DA0715-DA0717, # <u>38</u> Appendix DA0718-DA0719, # <u>39</u> Appendix DA0720-DA0722, # <u>40</u> Appendix DA0723-DA0732, # <u>41</u> Appendix DA0733-DA0740, # <u>42</u> Appendix DA0741-DA0749, # <u>43</u> Appendix DA0750-DA0769, # <u>44</u> Appendix DA0770-DA0781)(Rogowski, Patricia) (Entered: 06/25/2010)</p>
<p>CLAIM CONSTRUCTION OPENING BRIEF Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)</p>
<p>DECLARATION re <u>168</u> Claim Construction Opening Brief, Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010)</p>
<p>APPENDIX re <u>167</u> Claim Construction Opening Brief,,,,, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA-0001 - DA-0006, # <u>2</u> Appendix DA-0007 - DA-0032, # <u>3</u> Appendix DA-0033 - DA-0072, # <u>4</u> Appendix DA-0073 - DA-0112, # <u>5</u> Appendix DA-0113 - DA-0152, # <u>6</u> Appendix DA-0153 - DA-0192, # <u>7</u> Appendix DA-0193 - DA-0232, # <u>8</u> Appendix DA-0233 - DA-0272, # <u>9</u> Appendix DA-0273 - DA-0312, # <u>10</u> Appendix DA-0313 - DA-0352, # <u>11</u> Appendix DA-0353 - DA-0392, # <u>12</u> Appendix DA-0393 - DA-0432, # <u>13</u> Appendix DA-0433 - DA-0472, # <u>14</u> Appendix DA-0473 - DA-0512, # <u>15</u> Appendix DA-0513 - DA-0521)(Rogowski, Patricia) (Entered: 06/28/2010)</p>

<p>REDACTED VERSION of <u>175</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0522-DA0545, # <u>2</u> Appendix DA0546-DA0551, # <u>3</u> Appendix DA0552-DA0563, # <u>4</u> Appendix DA0564-DA0566, # <u>5</u> Appendix DA0567-DA0573, # <u>6</u> Appendix DA0574-DA0599, # <u>7</u> Appendix DA0600-DA0604, # <u>8</u> Appendix DA0605-DA0609, # <u>9</u> Appendix DA0610-DA0625, # <u>10</u> Appendix DA0626-DA0634, # <u>11</u> Appendix DA0635, # <u>12</u> Appendix DA0636-DA0652, # <u>13</u> Appendix DA0653-DA0657, # <u>14</u> Appendix DA0658-DA0667, # <u>15</u> Appendix DA0668-DA0670, # <u>16</u> Appendix DA0671-DA0678, # <u>17</u> Appendix DA0679-DA0687, # <u>18</u> Appendix DA0688-DA0696, # <u>19</u> Appendix DA0697-DA0705, # <u>20</u> Appendix DA0706-DA0711, # <u>21</u> Appendix DA0712-DA0714, # <u>22</u> Appendix DA0715-DA0717, # <u>23</u> Appendix DA0718-DA0719, # <u>24</u> Appendix DA0720-DA0722, # <u>25</u> Appendix DA0723-DA0732, # <u>26</u> Appendix DA0733-DA0740, # <u>27</u> Appendix DA0741-DA0749, # <u>28</u> Appendix DA0750-DA0769, # <u>29</u> Appendix DA0770-DA0781, # <u>30</u> Certificate of Service)(Rogowski, Patricia) (Entered: 06/28/2010)</p>
<p>NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (1) Vol. I - JA0001 to JA0533. APPENDIX VOL I. re <u>173</u> Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010).</p>
<p>NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (2) Vol. II - JA0534 to JA0930. APPENDIX VOL II. re 173 Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE). (lid) (Entered: 06/28/2010).</p>
<p>NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (3) Vol. III – JA0931 to JA1502. APPENDIX VOL III. re 173 Notice of Filing Paper Documents(OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010) (2 parts).</p>
<p>NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (4) Vol. IV – JA1503 to JA1510. APPENDIX VOL IV. re <u>173</u> Notice of Filing Paper Documents, (OVERSIZED DOCUMENT, ITEM ON FILE IN THE CLERKS OFFICE) (lid) (Entered: 06/28/2010).</p>
<p>NOTICE of filing the following document(s) in paper format: Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs (5) Vol. V – JA1511 to JA2089 (2 parts).</p>
<p>Vol. VI - JA2090 to JA2557. Original document(s) to be filed with the Clerk's Office. Notice filed by Denise Seastone Kraft on behalf of Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 06/25/2010).</p>
<p>MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)</p>
<p>MOTION for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)</p>
<p>OPENING BRIEF in Support re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)</p>
<p>OPENING BRIEF in Support re <u>187</u> MOTION for Partial Summary Judgment of Invalidity of the Asserted Aspar Patent Claims filed by MEMC Electronic Materials Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Rogowski, Patricia) (Entered: 07/02/2010)</p>

APPENDIX re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony Plaintiffs' Omnibus Appendix to Daubert Motion and Motions For Partial Summary Judgment Filed on July 2, 2010 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix Vol. II of XIX, # <u>2</u> Appendix Vol. III of XIX, # <u>3</u> Appendix Vol. IV of XIX, # <u>4</u> Appendix Vol. V of XIX, # <u>5</u> Appendix Vol. VII of XIX, # <u>6</u> Appendix Vol. IX of XIX, # <u>7</u> Appendix Vol. XI of XIX, # <u>8</u> Appendix Vol. XII of XIX, # <u>9</u> Appendix Vol. XIII of XIX, # <u>10</u> Appendix Vol. XIV of XIX, # <u>11</u> Appendix Vol. XV of XIX, # <u>12</u> Appendix Vol. XVI of XIX, # <u>13</u> Appendix Vol. XVIII of XIX, # <u>14</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Summary Judgment of Non-Infringement - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>206</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)

OPENING BRIEF in Support re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art - filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
MOTION for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/02/2010)
OPENING BRIEF in Support re <u>213</u> MOTION for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents filed by SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 7/19/2010. (Attachments: # <u>1</u> Certificate of Service)(Reed, John) (Entered: 07/02/2010)
REDACTED VERSION of <u>200</u> Opening Brief in Support, by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)
REDACTED VERSION of <u>201</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0001 - MA0004, # <u>2</u> Appendix MA0005 - MA0010, # <u>3</u> Appendix MA0011 - MA0016, # <u>4</u> Appendix MA0017 - MA0020, # <u>5</u> Appendix MA0021 - MA0029, # <u>6</u> Appendix MA0030 - MA0045, # <u>7</u> Appendix MA0046 - MA0052, # <u>8</u> Appendix MA0053 - MA0078, # <u>9</u> Appendix MA0079 - MA0092, # <u>10</u> Appendix MA0093 - MA0129, # <u>11</u> Appendix MA0130 - MA0148, # <u>12</u> Appendix MA0149 - MA0160, # <u>13</u> Appendix MA0161 - MA0163, # <u>14</u> Appendix MA0164 - MA0167, # <u>15</u> Appendix MA0168 - MA0172, # <u>16</u> Appendix MA0173 - MA0183, # <u>17</u> Appendix MA0184 - MA0196, # <u>18</u> Appendix MA0197 - MA0207, # <u>19</u> Appendix MA0208 - MA0241, # <u>20</u> Appendix MA0242 - MA0245, # <u>21</u> Appendix MA0246 - MA0249, # <u>22</u> Appendix MA0250 - MA0252, # <u>23</u> Appendix MA0253 - MA0265, # <u>24</u> Appendix MA0266 - MA0281, # <u>25</u> Appendix MA0282 - MA0312, # <u>26</u> Appendix MA0313 - MA0359, # <u>27</u> Appendix MA0360 - MA0365, # <u>28</u> Appendix MA0366, # <u>29</u> Appendix MA0367 - MA0400, # <u>30</u> Appendix MA0401 - MA0474, # <u>31</u> Appendix MA0475 - MA0483, # <u>32</u> Certificate)(Rogowski, Patricia) (Entered: 07/07/2010)

<p>REDACTED VERSION of <u>190</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0484 - MA0489, # <u>2</u> Appendix MA0490 - MA0515, # <u>3</u> Appendix MA0516 - MA0534, # <u>4</u> Appendix MA0535 - MA0541, # <u>5</u> Appendix MA0542 - MA0550, # <u>6</u> Appendix MA0551 - MA0561, # <u>7</u> Appendix MA0562 - MA0564, # <u>8</u> Appendix MA0565 - MA0569, # <u>9</u> Appendix MA0570 - MA0574, # <u>10</u> Appendix MA0575 - MA0576, # <u>11</u> Appendix MA0577 - MA0601, # <u>12</u> Appendix MA0602 - MA0603, # <u>13</u> Appendix MA0604 - MA0605, # <u>14</u> Appendix MA0606 - MA0609, # <u>15</u> Appendix MA0610 - MA0612, # <u>16</u> Appendix MA0613 - MA0625, # <u>17</u> Appendix MA0626 - MA0628, # <u>18</u> Appendix MA0629 - MA0630, # <u>19</u> Appendix MA0631 - MA0653, # <u>20</u> Appendix MA0654 - MA0685, # <u>21</u> Appendix MA0686 - MA0701, # <u>22</u> Appendix MA0702 - MA0732, # <u>23</u> Appendix MA0733 - MA0742, # <u>24</u> Appendix MA0743 - MA0750, # <u>25</u> Appendix MA0751 - MA0766, # <u>26</u> Appendix MA0767 - MA0772, # <u>27</u> Appendix MA0773 - MA0780, # <u>28</u> Appendix MA0781 - MA0807, # <u>29</u> Appendix MA0808 - MA0824, # <u>30</u> Appendix MA0825 - MA0831.1, # <u>31</u> Appendix MA0832 - MA0838, # <u>32</u> Appendix MA0839 - MA0844, # <u>33</u> Appendix MA0845 - MA0858, # <u>34</u> Appendix MA0859 - MA0868, # <u>35</u> Appendix MA0869 - MA0877, # <u>36</u> Appendix MA0878 - MA0884, # <u>37</u> Appendix MA0885 - MA0887, # <u>38</u> Appendix MA0888 - MA0891, # <u>39</u> Appendix MA0892 - MA0909, # <u>40</u> Appendix MA0910 - MA0931, # <u>41</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/07/2010)</p>
<p>REDACTED VERSION of <u>198</u> Opening Brief in Support,, SOITEC/CEA Parties' Opening Brief In Support Of Motion For Summary Judgment: Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)</p>
<p>REDACTED VERSION of <u>197</u> SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL)SEALED MOTION for Summary Judgment SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (FILED UNDER SEAL) SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/08/2010)</p>
<p>REDACTED VERSION of <u>192</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VI of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)</p>
<p>REDACTED VERSION of <u>193</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume VIII of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)</p>
<p>REDACTED VERSION of <u>194</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume X of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)</p>
<p>REDACTED VERSION of <u>195</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XVII of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)</p>
<p>REDACTED VERSION of <u>196</u> Appendix, Plaintiffs' Omnibus Appendix to Daubert Motion And Motions For Partial Summary Judgment Filed on July 2, 2010 - Volume XIX of XIX by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 07/09/2010)</p>
<p>CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)</p>

APPENDIX re <u>228</u> Claim Construction Answering Brief by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix DA0782 - DA0783, # <u>2</u> Appendix DA0784 - DA0785, # <u>3</u> Appendix DA0786, # <u>4</u> Appendix DA0787 - DA0810, # <u>5</u> Appendix DA0811 - DA0834, # <u>6</u> Appendix DA0835 - DA0845, # <u>7</u> Appendix DA0846 - DA0855, # <u>8</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/09/2010)
CLAIM CONSTRUCTION ANSWERING BRIEF re <u>168</u> Claim Construction Opening Brief, <u>228</u> Claim Construction Answering Brief Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
APPENDIX re <u>230</u> Claim Construction Answering Brief, Appendix to Plaintiffs S.O.I.TEC On Insulator Technologies, S.A. And Commissariat A Energie Atomique's Answering Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Appendix PA-0001 - PA-0050, # <u>2</u> Appendix PA-0051 - PA-0083, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/09/2010)
REDACTED VERSION of <u>183</u> Appendix, Joint Appendix of Exhibits to Opening and Answering Claim Construction Briefs Volume IV of VI by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
REDACTED VERSION of <u>170</u> Exhibit to a Document, Exhibit A to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
REDACTED VERSION of <u>171</u> Exhibit to a Document, Exhibit B to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
REDACTED VERSION of <u>172</u> Exhibit to a Document, Exhibit C to Declaration of Marcus T. Hall in Support of Plaintiffs S.O.I.TEC Silicon on Insulator Technologies, S.A. and Commissariat a L'Energie Atomique's Opening Claim Construction Brief by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/12/2010)
ANSWERING BRIEF in Opposition re <u>186</u> MOTION in Limine SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>208</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
ANSWERING BRIEF in Opposition re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)

ANSWERING BRIEF in Opposition re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 7/29/2010. (Rogowski, Patricia) (Entered: 07/19/2010)
APPENDIX re <u>247</u> Answering Brief in Opposition,, Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1156) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1103 - PA-1109 - FILED UNDER SEAL, # <u>2</u> Exhibit PA-1110 - PA-1118 - FILED UNDER SEAL, # <u>3</u> Exhibit PA-1119 - PA-1130 - FILED UNDER SEAL, # <u>4</u> Exhibit PA-1131 - PA-1143 - FILED UNDER SEAL, # <u>5</u> Exhibit PA-1144 - PA-1156, # <u>6</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)
APPENDIX re <u>250</u> Answering Brief in Opposition, Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1190 - PA-1191, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/19/2010)
REDACTED VERSION of <u>241</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
REDACTED VERSION of <u>249</u> Answering Brief in Opposition, to Plaintiffs' Motion for Summary Judgment on the Infringement of U.S. Patent No. 5,834,812 by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
REDACTED VERSION of <u>253</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Aspar Patents Are Not Invalid for Inequitable Conduct by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
REDACTED VERSION of <u>240</u> Appendix by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix MA0932 - MA0985, # <u>2</u> Appendix MA0986 - MA1039.22, # <u>3</u> Appendix MA1040 - MA1144, # <u>4</u> Appendix MA1145 - MA1200, # <u>5</u> Appendix MA1201 - MA1265, # <u>6</u> Appendix MA1265.1 - MA1338, # <u>7</u> Appendix MA1339 - MA1547, # <u>8</u> Appendix MA1548 - MA1627, # <u>9</u> Appendix MA1628 - MA1693, # <u>10</u> Appendix MA1694 - MA1953, # <u>11</u> Appendix MA1954 - MA2127, # <u>12</u> Appendix MA2128 - MA2206, # <u>13</u> Appendix MA2207 - MA2253, # <u>14</u> Appendix MA2254 - MA2273, # <u>15</u> Appendix MA2274 - MA2333, # <u>16</u> Appendix MA2334 - MA2337, # <u>17</u> Appendix MA2338 - MA2342, # <u>18</u> Appendix MA2343 - MA2346, # <u>19</u> Appendix MA2347 - MA2351, # <u>20</u> Certificate of Service)(Rogowski, Patricia) (Entered: 07/26/2010) (2 parts).
REDACTED VERSION of <u>261</u> Answering Brief in Opposition, to Plaintiffs' Motion for Partial Summary Judgment that the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents (CORRECTED VERSION OF D.I. 241) by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 07/26/2010)
REDACTED VERSION of <u>250</u> Answering Brief in Opposition, to Soitec's Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)
REDACTED VERSION of <u>247</u> Answering Brief in Opposition,, to Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of In validity Of The Asserted Aspar Claims by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/26/2010)
REDACTED VERSION of <u>254</u> Appendix,, to Appendix To Plaintiffs' Answering Brief In Opposition To Defendant's Motion For Partial Summary Judgment Of Invalidity Of The Asserted Aspar Claims (PA-1103 - PA-1143 by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)

REDACTED VERSION of <u>251</u> Appendix,, to Appendix to Plaintiffs' Answering Brief in Opposition to Defendant's Motion For Summary Judgment of Non-Infringement by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 07/26/2010)
REPLY BRIEF re <u>204</u> MOTION for Partial Summary Judgment Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
DECLARATION re <u>268</u> Reply Brief, Declaration of Marcus T. Hall in Support of Reply Brief in Support of Plaintiffs' Motion For Partial Summary Judgment That The Certificate of Correction For the '396 Patent is Valid by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
APPENDIX re <u>268</u> Reply Brief, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1261) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Exhibit PA-1199 - PA-1204, # <u>2</u> Exhibit PA-1205 - PA-1206, # <u>3</u> Exhibit PA-1206.1, # <u>4</u> Exhibit PA-1231 - PA-1237, # <u>5</u> Exhibit PA-1238 - PA-1245, # <u>6</u> Exhibit PA-1246 - PA-1257, # <u>7</u> Exhibit PA-1258 - PA-1261, # <u>8</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
REPLY BRIEF re <u>210</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment of Invalidity of United States Patent No. 5,834,812 For Lack of Enablement filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
REPLY BRIEF re <u>212</u> MOTION for Partial Summary Judgment SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art Reply Brief in Support of SOITEC's Motion For Partial Summary Judgment For Invalidity of Asserted Claims of United States Patent No. 5,834,812 in View of Prior Art filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
REPLY BRIEF re <u>202</u> MOTION for Partial Summary Judgment SOITEC/CEA Parties Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement Reply Brief in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Patents in Suit Satisfy The Written Description Requirement filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 07/30/2010)
REDACTED VERSION of <u>269</u> Appendix, TO REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2453_MA2479, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)
REDACTED VERSION of <u>273</u> Appendix REPLY BRIEF IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Appendix Table of Contents, # <u>2</u> Appendix MA2352 - MA2361, # <u>3</u> Appendix MA2362 - MA2371, # <u>4</u> Appendix MA2372 - MA2381, # <u>5</u> Appendix MA2382 - MA2391, # <u>6</u> Appendix MA2392 - MA2399, # <u>7</u> Appendix MA2400 - MA2404, # <u>8</u> Appendix MA2405 - MA2422, # <u>9</u> Appendix MA2423 - MA2425, # <u>10</u> Appendix MA2426 - MA2427, # <u>11</u> Appendix MA2428 - MA2430, # <u>12</u> Appendix MA2431 - MA2440, # <u>13</u> Appendix MA2441 - MA2448, # <u>14</u> Appendix MA2449 - MA2452, # <u>15</u> Appendix MA2452.1 - MA2452.9, # <u>16</u> Certificate of Service)(Rogowski, Patricia) (Entered: 08/03/2010)

REDACTED VERSION of <u>267</u> Reply Brief IN SUPPORT OF MEMC's MOTION FOR PARTIAL SUMMARY JUDGMENT OF INVALIDITY OF THE ASSERTED ASPAR PATENT CLAIMS by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)
REDACTED VERSION of <u>271</u> Reply Brief IN SUPPORT OF MEMC's MOTION FOR SUMMARY JUDGMENT OF NON-INFRINGEMENT by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 08/03/2010)
REDACTED VERSION of <u>274</u> Appendix,, Omnibus Appendix to Plaintiffs' Reply Briefs in Support of Plaintiffs' Daubert Motion and Motions For Partial Summary Judgment (PA-1192 - PA-1198 and PA-1207 - PA-1230 Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>277</u> Reply Brief, in Support of SOITEC/CEA Parties' Motion to Exclude The Expert Report of Dr. Pascal Bellon and Any Related Testimony by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>278</u> Reply Brief,, in Support of SOITEC/CEA Parties' Motion For Summary Judgment: Non-Infringement (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>279</u> Reply Brief,, in Support of Plaintiffs' Motion for Partial Summary Judgment That the Best Mode Requirement is Satisfied for the Claims of the '009 and '396 Patents (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>281</u> Reply Brief, in Support of Plaintiffs' Motion For Partial Summary Judgment That The Bruel Patent Does Not Anticipate The Aspar Patents (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
REDACTED VERSION of <u>282</u> Reply Brief,, in Support of SOITEC/CEA Parties' Motion For Partial Summary Judgment That The Aspar Patents Are Not Invalid For Inequitable Conduct (Filed Under Seal) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 08/06/2010)
NOTICE OF SERVICE of CD of documents MEMC0782194-MEMC0782500 and FH-1 0001 - FH-8 0067 by MEMC Electronic Materials Inc..(Rogowski, Patricia) (Entered: 09/16/2010)
REDACTED VERSION of <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>302</u> Declaration, of Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>303</u> Exhibit to a Document Exhibit A to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>304</u> Exhibit to a Document Exhibit B to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
REDACTED VERSION of <u>305</u> Exhibit to a Document Exhibit C to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)

REDACTED VERSION of <u>306</u> Exhibit to a Document Exhibit D to Michael L. Brody in Support of Motion to Reconsider Request to Modify Protective Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Kraft, Denise) (Entered: 09/24/2010)
Proposed Pretrial Order [Proposed] Joint Pretrial Order (FILED UNDER SEAL) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit 1 (Sealed), # <u>2</u> Exhibit 2A (Sealed), # <u>3</u> Exhibit 2B (Sealed), # <u>4</u> Exhibit 3A (Sealed), # <u>5</u> Exhibit 3B (Sealed), # <u>6</u> Exhibit 4A (Sealed), # <u>7</u> Exhibit 4B (Sealed), # <u>8</u> Exhibit 4C (Sealed), # <u>9</u> Exhibit 5A (Sealed), # <u>10</u> Exhibit 5B (Sealed), # <u>11</u> Exhibit 6A (Sealed), # <u>12</u> Exhibit 6B (Sealed), # <u>13</u> Exhibit 7A (Sealed), # <u>14</u> Exhibit 7B (Sealed), # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 10/07/2010)
Proposed Voir Dire by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 10/08/2010)
VERDICT SHEET by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 10/08/2010)
Proposed Voir Dire by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/08/2010)
VERDICT SHEET by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 10/08/2010)
Proposed Jury Instructions by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/08/2010)
Proposed Jury Instructions by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/08/2010)
REDACTED VERSION of <u>315</u> Proposed Pretrial Order,, Redacted Version of [Proposed] Joint Pretrial Order by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2A, # <u>3</u> Exhibit 2B, # <u>4</u> Exhibit 3A, # <u>5</u> Exhibit 3B, # <u>6</u> Exhibit 4A, # <u>7</u> Exhibit 4B, # <u>8</u> Exhibit 4C, # <u>9</u> Exhibit 5A, # <u>10</u> Exhibit 5B, # <u>11</u> Exhibit 6A, # <u>12</u> Exhibit 6B, # <u>13</u> Exhibit 7A, # <u>14</u> Exhibit 7B, # <u>15</u> Certificate of Service)(Kraft, Denise) (Entered: 10/13/2010)
MEMORANDUM OPINION. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010)
ORDER denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment ; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010)
MEMORANDUM ORDER re: claim construction. Signed by Judge Sue L. Robinson on 10/13/2010. (nmf) (Entered: 10/13/2010) ORAL ORDER by Judge Sue L. Robinson on 10/14/2010 that the responses to the issues raised in the exhibits to the joint pre-trial order are to be stricken from the record. (These filings, formerly D.I. Nos. 318 and 323 have been deleted from the docket.) (nmf) (Entered: 10/14/2010)

<p>AMENDED ORDER denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment ; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; *granting* <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/14/2010. (nmf) (Entered: 10/14/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Final Pretrial Conference held on 10/14/2010. (Court Reporter V. Gunning.) (nmf) (Entered: 10/15/2010) SO ORDERED, re <u>315</u> Proposed Pretrial Order. Signed by Judge Sue L. Robinson on 10/14/2010. (nmf) (Entered: 10/15/2010)</p>
<p>MOTION for Reargument re <u>327</u> Memorandum and Order - Reargument of Claim Construction of One Claim Term of U.S. Patent 6,809,009 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 10/18/2010)</p>
<p>SECOND AMENDED ORDER re: <u>325</u> denying <u>141</u> Motion for Discovery; denying <u>186</u> Motion in Limine; granting in part and denying in part <u>187</u> Motion for Partial Summary Judgment; granting <u>197</u> Motion for Summary Judgment ; granting <u>199</u> Motion for Summary Judgment **with respect to the '484 patent and with respect to its current process, and denied in other respects; granting <u>202</u> Motion for Partial Summary Judgment; denying <u>204</u> Motion for Partial Summary Judgment; denying <u>206</u> Motion for Partial Summary Judgment; granting in part and denying in part <u>208</u> Motion for Partial Summary Judgment; denying <u>210</u> Motion for Partial Summary Judgment; denying <u>212</u> Motion for Partial Summary Judgment; granting <u>213</u> Motion for Partial Summary Judgment. Signed by Judge Sue L. Robinson on 10/19/2010. (nmf) (Entered: 10/19/2010)</p>
<p>MEMORANDUM ORDER granting <u>329</u> MOTION for Reargument re <u>327</u> Memorandum and Order - Reargument of Claim Construction of One Claim Term of U.S. Patent 6,809,009. Signed by Judge Sue L. Robinson on 10/19/2010. (nmf) (Entered: 10/19/2010)</p>
<p>STIPULATION MEMC's Declaratory Judgment counterclaim asserting invalidity of United States Reissued Patent No. 39,484 in Civil Action No. 1:08-292-SLR is dismissed without prejudice by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (nmf,). (Entered: 10/21/2010)</p>
<p>STIPULATION of Fact re <u>331</u> Memorandum and Order, <u>327</u> Memorandum and Order, <u>325</u> Memorandum Opinion by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 10/21/2010)</p>
<p>Letter to The Honorable Sue L. Robinson from Denise Seastone Kraft regarding Mutually agreed upon narrowing of the issues for trial - re <u>333</u> Stipulation, <u>332</u> Stipulation,. (Kraft, Denise) (Entered: 10/21/2010) CORRECTING ENTRY: The pdf of D.I. <u>332</u> has been replaced with the correct pdf of the stipulation per request of filer. (nmf) (Entered: 10/22/2010) SO ORDERED, re <u>333</u> Stipulation filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique, <u>332</u> Stipulation, filed by SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc., Commissariat a LEnergie Atomique. Signed by Judge Sue L. Robinson on 10/22/2010. (nmf) (Entered: 10/22/2010)</p>
<p>Voir Dire Questions. Read in Open Court 10/25/2010.(nmf) (Entered: 10/25/2010)</p>
<p>Preliminary Jury Instructions. Read in Open Court 10/25/2010. (nmf) (Entered: 10/25/2010) Minute Entry for proceedings held before Judge Sue L. Robinson: Jury Trial Day 1 held on 10/25/2010. (Court Reporter Valerie Gunning, Brian Gaffigan.) (dlk) (Entered: 10/26/2010)</p>
<p>PLAINTIFF'S BENCH MEMORANDUM. Filed in Court 10/26/2010. (nmf) (Entered: 10/26/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial (Day 2) held on 10/26/2010. (Court Reporter Valerie Gunning, Kevin Maurer.) (dlk) (Entered: 10/26/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial - Day 3, held on 10/27/2010. (Court Reporter Valerie Gunning/Kevin Maurer.) (nms) (Entered: 10/27/2010)</p>

STATEMENT -- BENCH MEMORANDUM SUPPORTING MEMC'S PROFFER OF ADMISSIONS BY SOITEC IN PRIOR LAWSUIT INVOLVING THE '564 PATENT submitted at trial by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit A)(Rogowski, Patricia) (Entered: 10/28/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial - Day 4 held on 10/28/2010. (Court Reporter Valerie Gunning/Kevin Maurer.) (nms) (Entered: 11/01/2010)
Final Jury Instructions read in open Court by Judge Robinson. (lid) (Entered: 11/01/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial held on 11/1/2010. (DAY 5) (Court Reporter V. Gunning.) (lid) (Entered: 11/02/2010) Minute Entry for proceedings held before Judge Sue L. Robinson - Jury Trial completed on 11/2/2010. (DAY 6) (Court Reporter V. Gunning.) (lid) (Entered: 11/02/2010)
REDACTED VERSION of <u>342</u> Jury Verdict. (lid) (Entered: 11/02/2010)
STATEMENT Bench Memorandum in Support of Plaintiffs' Motion For Judgment as a Matter of Law of No Unenforceability of the '009 Patent Due To Inequitable Conduct submitted at trial by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/02/2010)
ANSWERING BRIEF in Opposition re <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order (MEMC'S OPPOSITION TO PLAINTIFFS' MOTION FOR REARGUMENT RE: MODIFICATION OF THE PROTECTIVE ORDER) filed by MEMC Electronic Materials Inc.. Reply Brief due date per Local Rules is 11/22/2010. (Attachments: # <u>1</u> Exhibit 1 through 5, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 11/12/2010)
JUDGMENT in favor of defendant MEMC Electronic Materials, Inc. and against plaintiffs S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat A LEnergie Atomique et aux Energies Alternatives as to the 812 patent. IT IS FURTHER ORDERED that judgment be and is hereby entered in favor of plaintiffs S.O.I.TEC Silicon On Insulator Technologies, S.A. and Commissariat A LEnergie Atomique et aux Energies Alternatives and against defendant MEMC Electronic Materials, Inc. as to the 009 patent. Signed by Judge Sue L. Robinson on 11/15/2010. (nmf) (Entered: 11/15/2010)
STIPULATION Setting Post-Trial Briefing Schedule re <u>348</u> Judgment,, by Commissariat a LEnergie Atomique, MEMC Electronic Materials Inc., SOITEC Silicon On Insulator Technologies SA. (Rogowski, Patricia) (Entered: 11/15/2010)
MOTION for Reargument re <u>348</u> Judgment,, (MEMCS MOTION FOR REARGUMENT OF THE COURTS ORDER RE: THE UNENFORCEABILITY OF THE 009 PATENT) - filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1)(Rogowski, Patricia) (Entered: 11/16/2010) SO ORDERED- re <u>349</u> Stipulation. Set POST TRIAL Briefing Schedule: (Opening Brief due 12/8/2010., Answering Brief due 12/29/2010., Reply Brief due 1/12/2010.). Signed by Judge Sue L. Robinson on 11/17/2010. (lid) (Entered: 11/17/2010)
MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2010)
OPENING BRIEF in Support re <u>301</u> SEALED MOTION for Reconsideration Request to Modify Protective Order, <u>351</u> MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. Answering Brief/Response due date per Local Rules is 12/10/2010. (Attachments: # <u>1</u> Appendix A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 11/23/2010)
STIPULATION TO EXTEND TIME Respond to MEMC's Motion for Reargument of the Court's Order Re: Unenforceability of the '009 Patent to December 3, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 11/24/2010) SO ORDERED- re <u>353</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: re <u>350</u> MOTION for Reargument re <u>348</u> Judgment,. (Answering Brief due 12/3/2010.). Signed by Judge Sue L. Robinson on 11/30/2010. (lid) (Entered: 11/30/2010)

STIPULATION TO EXTEND TIME to file Motions and Opening Post-Trial Briefs to December 13, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/03/2010)
REPLY BRIEF re <u>350</u> MOTION for Reargument re <u>348</u> Judgment,, (MEMCS MOTION FOR REARGUMENT OF THE COURTS ORDER RE: THE UNENFORCEABILITY OF THE 009 PATENT) Plaintiffs' Opposition to MEMC's Motion For Reargument of the Court's Order Re: The Unenforceability of the '009 Patent filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/03/2010) SO ORDERED- re <u>354</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: (POST TRIAL Opening Brief due 12/13/2010.). Signed by Judge Sue L. Robinson on 12/6/2010. (lid) (Entered: 12/06/2010)
EXHIBIT re <u>355</u> Reply Brief, Exhibit B to Plaintiffs' Opposition to MEMC's Motion For Reargument of the Court's Order Re: The Unenforceability of the '009 Patent by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/06/2010)
ANSWERING BRIEF in Opposition re <u>351</u> MOTION for Leave to File Reply in Support of Plaintiff's Motion for Reargument filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 12/20/2010. (Rogowski, Patricia) (Entered: 12/10/2010)
STIPULATION TO EXTEND TIME Stipulation and Order for Plaintiffs to file Motions and Opening Post-Trial Briefs to December 14, 2010 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 12/13/2010)
MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/13/2010)
OPENING BRIEF in Support re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by MEMC Electronic Materials Inc..Answering Brief/Response due date per Local Rules is 12/30/2010. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Certificate of Service)(Rogowski, Patricia) (Entered: 12/13/2010)
MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
OPENING BRIEF in Support re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA.Answering Brief/Response due date per Local Rules is 1/3/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
MOTION For Injunctive Relief Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA. (Attachments: # <u>1</u> Text of Proposed Order, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 12/14/2010)
STIPULATION TO EXTEND TIME due date for Answering and Reply Post-Trial Briefs to January 7, 2011 for Answering Brief and January 21, 2011 for Reply Brief - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 12/15/2010) SO ORDERED- re <u>365</u> STIPULATION TO EXTEND TIME. Set Briefing Schedule: (Answering Post trial Brief due 1/7/2011., Reply post trial Brief due 1/21/2011.). Signed by Judge Sue L. Robinson on 12/16/2010. (lid) (Entered: 12/17/2010)
STIPULATION TO EXTEND TIME Post-Trial Answering Briefs to January 12, 2011 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/06/2011)
NOTICE of Appearance by Aleine Michelle Porterfield on behalf of Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc. (Attachments: # <u>1</u> Certificate of Service)(Porterfield, Aleine) (Entered: 01/07/2011)

Joint STIPULATION TO EXTEND TIME Post-trial Answering Briefs and Post-trial Reply Briefs to January 14, 2011 and January 28, 2011 - filed by MEMC Electronic Materials Inc.. (Rogowski, Patricia) (Entered: 01/12/2011)
ANSWERING BRIEF in Opposition re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc..Reply Brief due date per Local Rules is 1/24/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 01/14/2011).
ANSWERING BRIEF in Opposition re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial (MEMCS ANSWERING BRIEF IN OPPOSITION TO PLAINTIFFS RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL) filed by MEMC Electronic Materials Inc..Reply Brief due date per Local Rules is 1/24/2011. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/14/2011).
DECLARATION re <u>378</u> Answering Brief in Opposition, (DECLARATION OF ROBERT M. EVANS, JR. IN SUPPORT OF MEMCS OPPOSITION TO PLAINTIFFS RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL) by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1, # <u>2</u> Exhibit 2, # <u>3</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/14/2011)
REDACTED VERSION of <u>376</u> Answering Brief in Opposition, to Plaintiffs' Motion for Injunctive Relief and to Lift Stay on Damages Discovery by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/20/2011)
REDACTED VERSION of <u>377</u> Appendix to MEMC's Answering Brief in Opposition to Plaintiffs' Motion for Injunctive Relief and to Lift Stay on Damages Discovery by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Exhibit 1-7, # <u>2</u> Exhibit 8, # <u>3</u> Exhibit 9, # <u>4</u> Exhibit 10, # <u>5</u> Exhibit 11, # <u>6</u> Exhibit 12-13, # <u>7</u> Exhibit 14, # <u>8</u> Exhibit 15, # <u>9</u> Exhibit 16, # <u>10</u> Exhibit 17, # <u>11</u> Exhibit 18, # <u>12</u> Exhibit 19, # <u>13</u> Certificate of Service)(Rogowski, Patricia) (Entered: 01/20/2011)
Joint STIPULATION TO EXTEND TIME of Post-Trial Reply Briefs to Tuesday, February 1, 2011 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 01/28/2011)
Joint STIPULATION TO EXTEND TIME of Post-Trial Reply Briefs to Friday, February 4, 2011 - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 01/31/2011)
REDACTED VERSION of <u>364</u> Opening Brief in Support,,,, Redacted Version of Opening Brief in Support of Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Exhibit B, # <u>3</u> Exhibit C, # <u>4</u> Exhibit D, # <u>5</u> Exhibit E, # <u>6</u> Exhibit F, # <u>7</u> Exhibit G, # <u>8</u> Exhibit H, # <u>9</u> Exhibit I, # <u>10</u> Exhibit J, # <u>11</u> Exhibit K, # <u>12</u> Exhibit L, # <u>13</u> Exhibit M, # <u>14</u> Exhibit N, # <u>15</u> Exhibit O, # <u>16</u> Exhibit P, # <u>17</u> Exhibit Q, # <u>18</u> Exhibit R, # <u>19</u> Exhibit S)(Kraft, Denise) (Entered: 02/02/2011)
REPLY BRIEF re <u>359</u> MOTION for Judgment as a Matter of Law - MEMC'S RENEWED MOTION FOR JUDGMENT AS A MATTER OF LAW OR IN THE ALTERNATIVE FOR A NEW TRIAL filed by MEMC Electronic Materials Inc.. (Attachments: # <u>1</u> Certificate of Service)(Rogowski, Patricia) (Entered: 02/04/2011)
REPLY BRIEF re <u>361</u> MOTION for Judgment as a Matter of Law Plaintiffs' Renewed Motion For Judgment As A Matter of Law Or In The Alternative For A New Trial filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/04/2011)

DECLARATION re <u>387</u> Reply Brief, Declaration of Michael L. Brody in Support of Reply Brief In Support of Plaintiffs' Renewed Motion For Judgment as a Matter of Law or In The Alternative For a New Trial by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 02/04/2011)
MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) - filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)
OPENING BRIEF in Support re <u>390</u> MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) MOTION to Strike <u>386</u> Reply Brief, Motion By Plaintiffs' To Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) filed by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. Answering Brief/Response due date per Local Rules is 2/25/2011. (Attachments: # <u>1</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)
DECLARATION re <u>391</u> Opening Brief in Support,, Declaration of Marcus T. Hall in Support of Plaintiffs' Opening Brief in Support of Motion to Strike Reply Brief In Support of MEMC's Renewed Motion For Judgment as a Matter of Law or, In The Alternative, a New Trial (D.I. 386) by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Attachments: # <u>1</u> Exhibit A, # <u>2</u> Certificate of Service)(Kraft, Denise) (Entered: 02/08/2011)
REDACTED VERSION of <u>389</u> Reply Brief, Redacted Version of Reply Brief in Support of Plaintiffs' Motion For Injunctive Relief And To Lift Stay on Damages Discovery by Commissariat a LEnergie Atomique, SOITEC Silicon On Insulator Technologies SA, SOITEC U.S.A., Inc.. (Kraft, Denise) (Entered: 02/09/2011)

Applicants are enclosing Form PTO-1449(forty eight), along with a copy of each listed reference for which a copy is required under 37 CFR §1.98(a)(2). Pursuant to the undersigned attorney's obligation and duties under 37 CFR §§ 1.56 and 1.98(a)(3) and (c), either English language abstracts, partial translations, or full translations are included for patent documents which are not in English for the express purpose of providing a concise explanation of the references to the Patent and Trademark Office with the opportunity to evaluate the same.

References D470 – D499 are cited in accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and, more particularly, in accordance with 37 C.F.R. §1.97(b). These documents are litigation documents filed by the parties in *SOITEC SA v. SILICON GENESIS* (2003-1080) in the U.S. Court of Appeal for the Federal Circuit. This litigation involved U.S. Pat. No. 5,374,564, owned by the assignee of record herein.

References D500 – D676 are cited in accordance with the duty of disclosure under 37 C.F.R. §1.56 and §§1.97-1.98, and, more particularly, in accordance with 37 C.F.R. §1.97(b). These documents are litigation documents filed by the parties in *SOITEC SA v. MEMC* (1:08-cv-00292-SLR) in the U.S. District Court, District of Delaware. This lawsuit involves patents owned by the assignee of record, including Re39,484, which is a reissue patent of U.S. Pat. No. 5,374,564, and including other patents that disclose subject matter that may be related to that claimed in the above-referenced patent application. Applicants respectfully request the Examiner's consideration of the above reference(s) and entry thereof into the record of this application.

By submitting this Statement, Applicants are attempting to fully comply with the duty of candor and good faith mandated by 37 CFR §1.56. As such, this Statement is not intended to constitute an admission that any of the enclosed references, or other information referred to therein, constitutes “prior art” or is otherwise “material to patentability,” as that phrase is defined in 37 CFR §1.56(a).

The Applicant or Applicants have calculated no fee to be due in connection with the filing of this Information Disclosure Statement. However, the Director is authorized to charge any fee deficiency associated with the filing of this Information Disclosure Statement to a deposit account, as authorized in the Transmittal accompanying this Information Disclosure Statement.

Respectfully submitted,

March 18, 2011

Date

/Jasper W. Dockrey/

Jasper W. Dockrey
(Reg. No. 33,868)